

Erratum: "Observation of two-dimensional electron gas in a Si quantum well with mobility of $1.6 \times 10^6 \text{ cm}^2/\text{Vs}$ " [Appl. Phys. Lett. 94, 182102 (2009)]

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Erratum: “Observation of two-dimensional electron gas in a Si quantum well with mobility of 1.6×10^6 cm²/V s” [Appl. Phys. Lett. 94, 182102 (2009)]

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A cross-sectional transmission electron micrograph (Fig. 1) of the sample used in the study shows that the thickness of the SiGe barrier layer is 150 nm, not 65 nm as shown in the paper. The other parts of the paper remain unchanged. The difference in the barrier layer thickness does not affect the conclusions of the article.

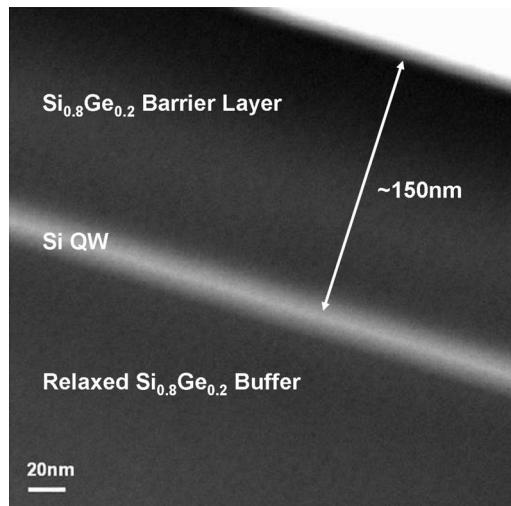


FIG. 1. A cross-sectional transmission electron micrograph of the sample used in the study; the thickness of the SiGe barrier layer is 150 nm.

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